






	<h2>IRFBE30SPBF</h2>
	<p>Hersteller-Teilenummer: IRFBE30SPBF</p> <p>Hersteller / Marke: Electro-Films (EFI) / Vishay</p> <p>Teil der Beschreibung: MOSFET N-CH 800V 4.1A D2PAK</p> <p>Datenblätter:  IRFBE30SPBF.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 2400 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	IRFBE30SPBF
Hersteller	Electro-Films (EFI) / Vishay
Beschreibung	MOSFET N-CH 800V 4.1A D2PAK
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs ,
Teilstatus	2400 pcs Stock
Hersteller Standard Vorlaufzeit	18 Weeks
detaillierte Beschreibung	N-Channel 800V 4.1A (Tc) 125W (Tc) Surface Mount
Serie	-
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Verpackung / Gehäuse	TO-263-3, D ² Pak (2 Leads + Tab), TO-263AB
Supplier Device-Gehäuse	D2PAK
Verlustleistung (max)	125W (Tc)
Typ FET	N-Channel
FET-Merkmal	-
Drain-Source-Spannung (Vdss)	800V
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	4.1A (Tc)
Rds On (Max) @ Id, Vgs	3 Ohm @ 2.5A, 10V
VGS (th) (Max) @ Id	4V @ 250µA
Gate Charge (Qg) (Max) @ Vgs	78nC @ 10V
Eingabekapazität (Ciss) (Max) @ Vds	1300pF @ 25V
Antriebsspannung (Max Rds On, Min Rds On)	10V
Vgs (Max)	±20V
Verpackung	Tube
Bleifreier Status / RoHS-Status	Lead free / RoHS Compliant
Feuchtigkeitsempfindlichkeitsniveau (MSL)	1 (Unlimited)
Andere Namen	*IRFBE30SPBF

IRFBE30SPBF ist neu im Original. Suche IRFBE30SPBF Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie IRFBE30SPBF Electro-Films (EFI) / Vishay mit Garantie und Vertrauen. Anfrage IRFBE30SPBF: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>IRFBE30PBF Electro-Films (EFI) / Vishay MOSFET N-CH 800V 4.1A TO-220AB</p>	 <p>IRFBE30SPBF Vishay / Siliconix MOSFET N-CH 800V 4.1A D2PAK</p>	 <p>IRFBE30STRLPBF Electro-Films (EFI) / Vishay MOSFET N-CH 800V 4.1A D2PAK</p>	 <p>IRFBE30STRLPBF Vishay / Siliconix MOSFET N-CH 800V 4.1A D2PAK</p>
 <p>IRFBE30PBF Vishay / Siliconix MOSFET N-CH 800V 4.1A TO-220AB</p>	 <p>IRFBE30LPBF-M IR IRFBE30LPBF-M IR</p>	 <p>IRFBE30STRL Vishay / Siliconix MOSFET N-CH 800V 4.1A D2PAK</p>	 <p>IRFBE30S Electro-Films (EFI) / Vishay MOSFET N-CH 800V 4.1A D2PAK</p>

heiße Teile

Mehr

 IRFBC40LC	 IRFBC40S	 IRFBC40LCPBF	 IRFBC40SPBF	 IRFBC40LPBF
 IRFBC40LPBF	 IRFBC40STRL	 IRFBC40S	 IRFBC40STRLPBF	 IRFBC40SPBF
 IRFBC40STRL	 IRFBC41LC	 IRFBC40STRLPBF	 IRFBC40STRLPBF	 IRFBC40STRR
 IRFBC40STRR	 IRFBE20PBF	 IRFBE20PBF	 IRFBE20PBF	 IRFBE20SPBF
 IRFBE30L	 IRFBE30LPBF-M	 IRFBE30LPBF-M	 IRFBE30PBF	 IRFBE30PBF
 IRFBE30SPBF	 IRFBE30STRLPBF	 IRFBE30STRLPBF	 IRFBE30PBF	 IRFBE30PBF
 IRFBE30STRL	 IRFBE30STRLPBF	 IRFBE30STRLPBF	 IRFBE30PBF	 IRFBE30PBF
 IRFBG20PBF	 IRFBF20STRL	 IRFBF20STRLPBF	 IRFBF20LPBF	 IRFBF20LPBF
 IRFD010PBF	 IRFBG30PBF	 IRFBG30PBF	 IRFBF20STRLPBF	 IRFBG20PBF
 IRFD110PBF	 IRFD010PBF	 IRFD020PBF	 IRFBL10N60A	 IRFC480LCD
	 IRFD120PBF	 IRFD120PBF	 IRFD020PBF	 IRFD110PBF
			 IRFD12N06RLESM	 IRFD210PBF

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